



October 2014

FDMS86102LZ

N-Channel Shielded Gate PowerTrench[®] MOSFET

100 V, 22 A, 25 mΩ

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 25 mΩ at V_{GS} = 10 V, I_D = 7 A
- Max $r_{DS(on)}$ = 37 mΩ at V_{GS} = 4.5 V, I_D = 5.8 A
- HBM ESD protection level > 6 kV typical (Note 4)
- 100% UIL Tested
- RoHS Compliant



General Description

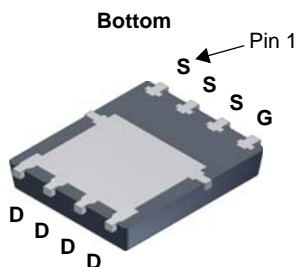
This N-Channel logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench[®] process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance. G-S zener has been added to enhance ESD voltage level.

Applications

- DC - DC Conversion
- Inverter
- Synchronous Rectifier

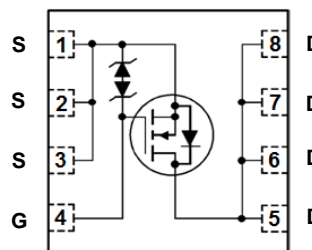


Top



Bottom

Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$	22	A
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	7	
	-Pulsed	40	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	84	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	69	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86102Z	FDMS86102LZ	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		70		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.0	1.5	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		-6		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 7\text{ A}$		18.6	25	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 5.8\text{ A}$		23.5	37	
		$V_{GS} = 10\text{ V}$, $I_D = 7\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		31.2	42	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 7\text{ A}$		26		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		979	1305	pF
C_{oss}	Output Capacitance			175	235	pF
C_{rss}	Reverse Transfer Capacitance			8.9	15	pF
R_g	Gate Resistance			0.9		Ω

Switching Characteristics

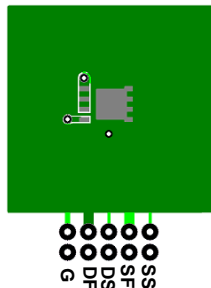
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		6.7	14	ns
t_r	Rise Time			2.6	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	35	ns
t_f	Fall Time			2.5	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 50\text{ V}$, $I_D = 7\text{ A}$	16	22	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$		7.8	11	nC
Q_{gs}	Total Gate Charge			2.4		nC
Q_{gd}	Gate to Drain "Miller" Charge			2.6		nC

Drain-Source Diode Characteristics

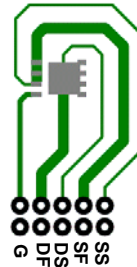
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 7\text{ A}$ (Note 2)		0.81	1.3	V
		$V_{GS} = 0\text{ V}$, $I_S = 2\text{ A}$ (Note 2)		0.72	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		35	57	ns
Q_{rr}	Reverse Recovery Charge			25	40	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 50 $^{\circ}\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. 125 $^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. Starting $T_J = 25\text{ }^{\circ}\text{C}$; N-ch: $L = 1\text{ mH}$, $I_{AS} = 13\text{ A}$, $V_{DD} = 90\text{ V}$, $V_{GS} = 10\text{ V}$.

4. The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

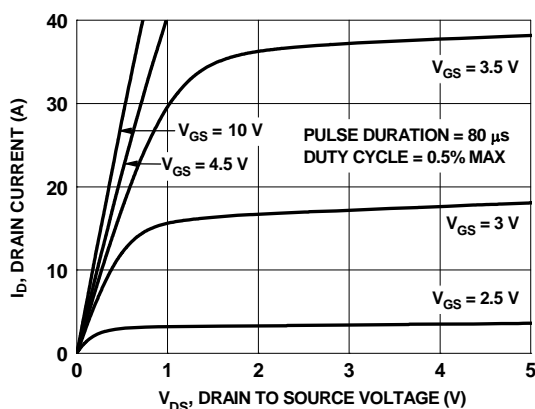


Figure 1. On-Region Characteristics

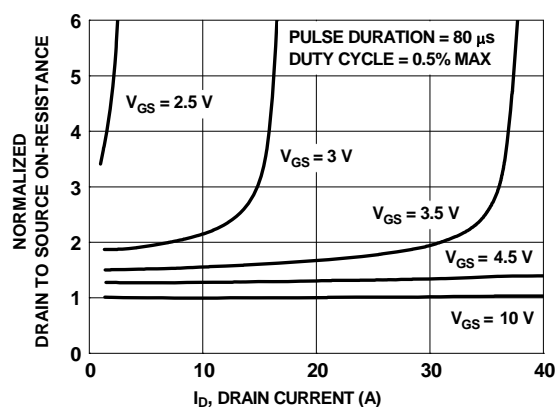


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

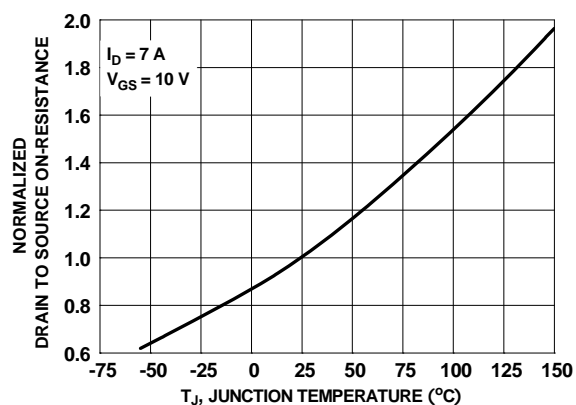


Figure 3. Normalized On-Resistance vs Junction Temperature

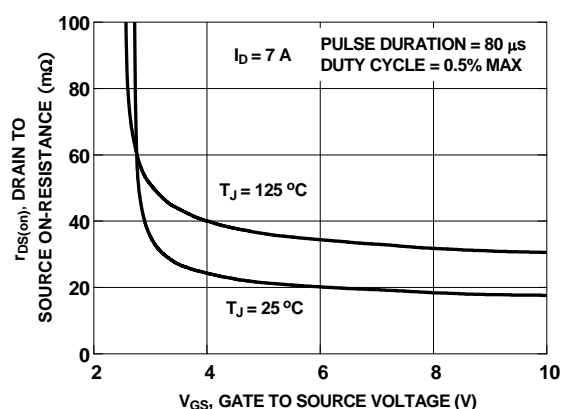


Figure 4. On-Resistance vs Gate to Source Voltage

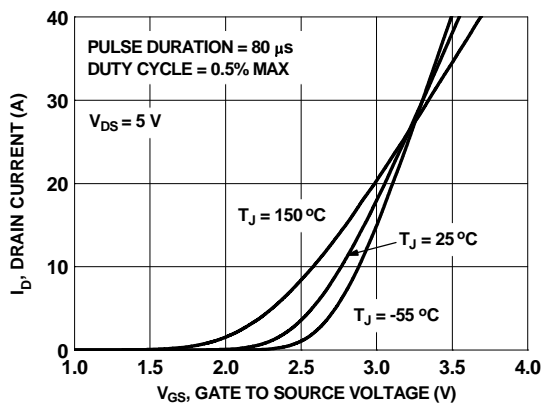


Figure 5. Transfer Characteristics

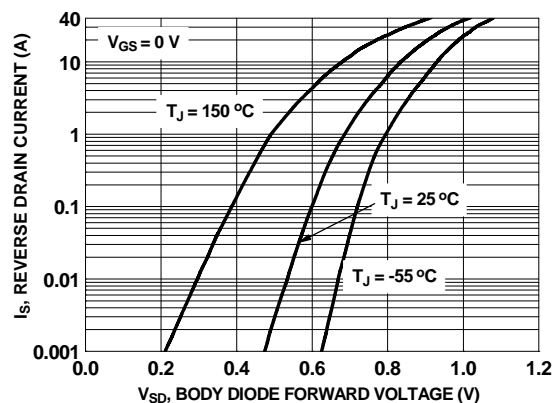


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

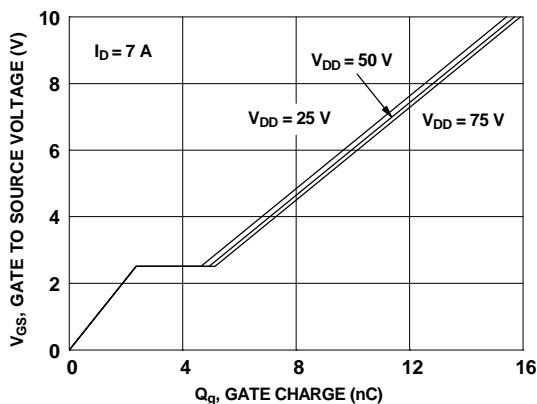


Figure 7. Gate Charge Characteristics

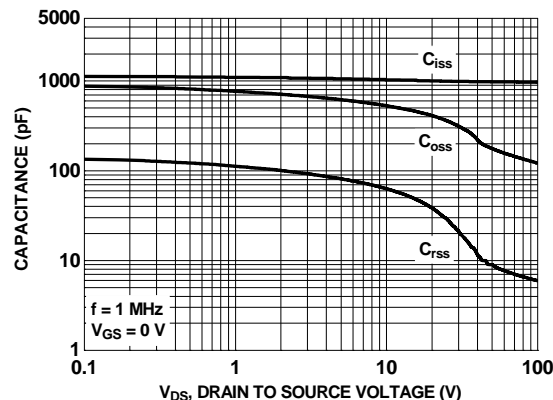


Figure 8. Capacitance vs Drain to Source Voltage

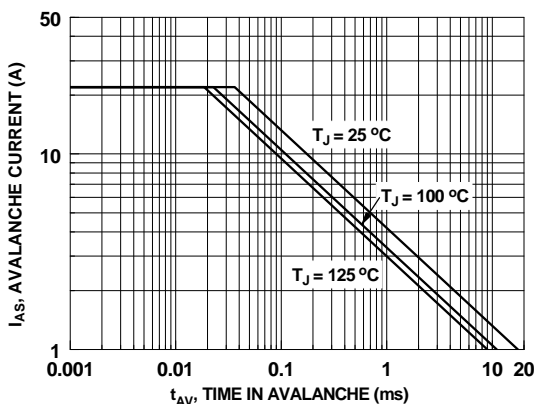


Figure 9. Unclamped Inductive Switching Capability

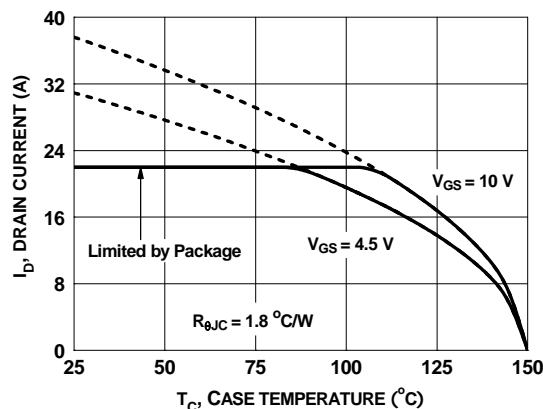


Figure 10. Maximum Continuous Drain Current vs Case Temperature

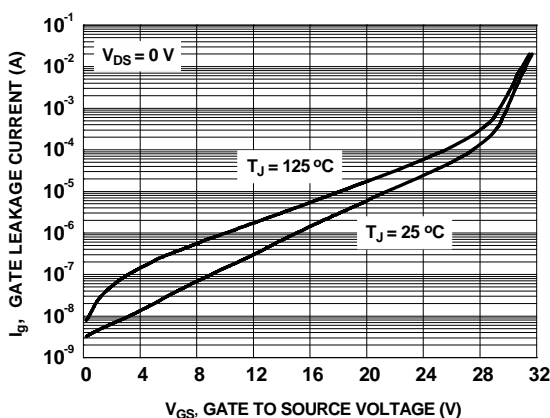


Figure 11. Gate Leakage Current vs Gate to Source Voltage

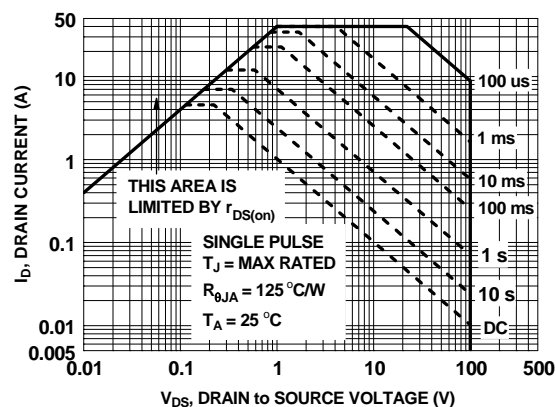


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

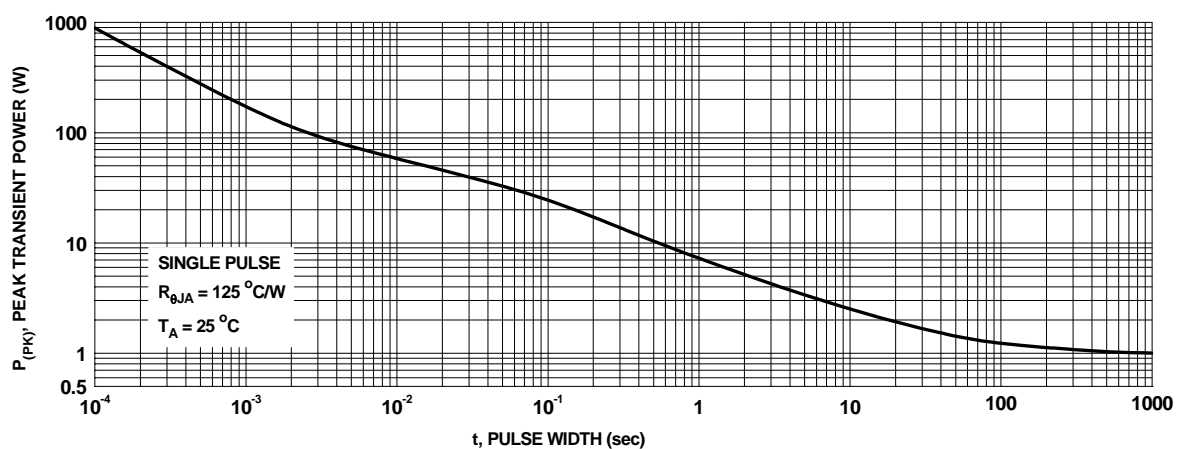


Figure 13. Single Pulse Maximum Power Dissipation

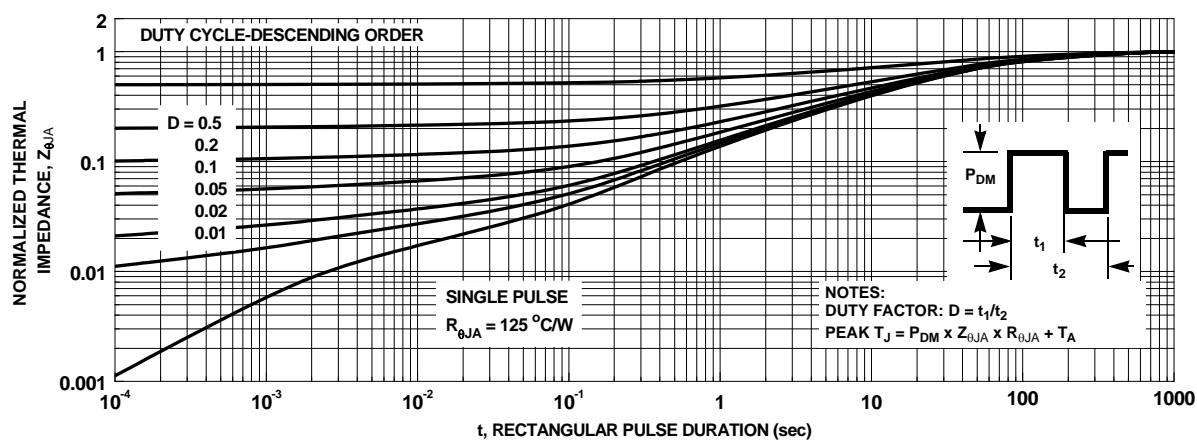
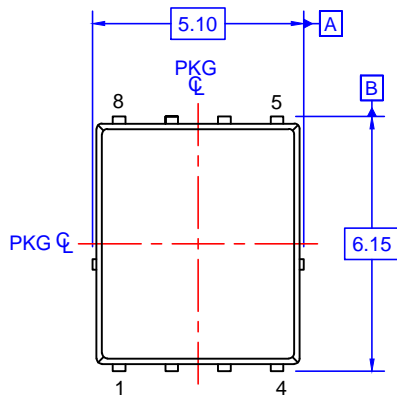
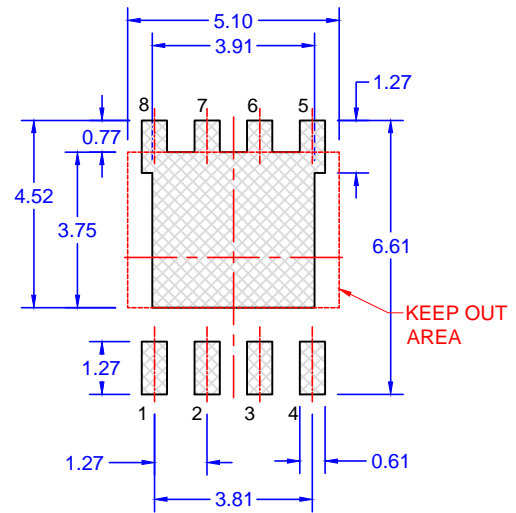
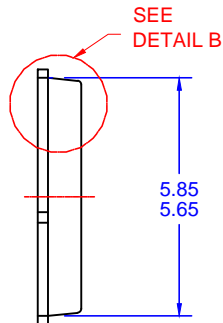


Figure 14. Junction-to-Ambient Transient Thermal Response Curve

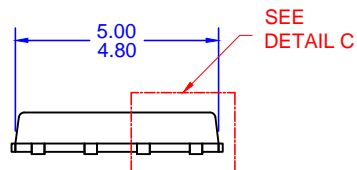
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



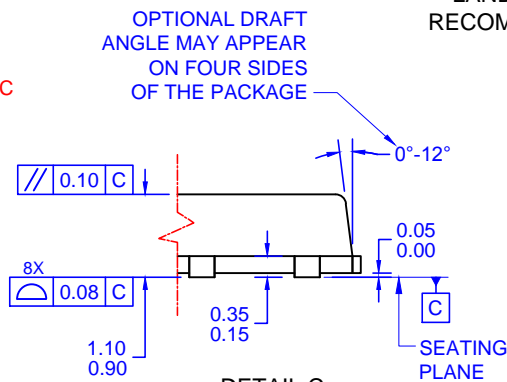
TOP VIEW



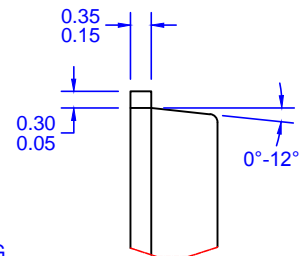
LAND PATTERN
RECOMMENDATION



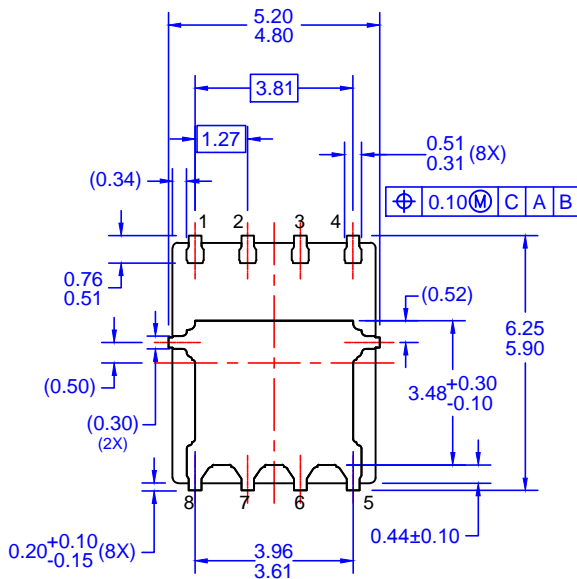
SIDE VIEW



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,.
- DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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